

Supporting information for “Diameter-dependent internal gain in ZnO  
micronanowires under electron beam irradiation”

Qi Zhang,<sup>1</sup> Junjie Qi,<sup>1</sup> Xin Li,<sup>1</sup> Yue Zhang,<sup>1,2,a</sup>

<sup>1</sup>Department of Materials physics and Chemistry, University of Science and  
Technology Beijing, 30 Xueyuan Road, Haidian District, Beijing 100083, China

<sup>2</sup>State Key Laboratory for Advanced Metals and Materials, University of Science and  
Technology Beijing, 30 Xueyuan Road, Haidian District, Beijing 100083, China

E-mail: [yuezhang@ustb.edu.cn](mailto:yuezhang@ustb.edu.cn)

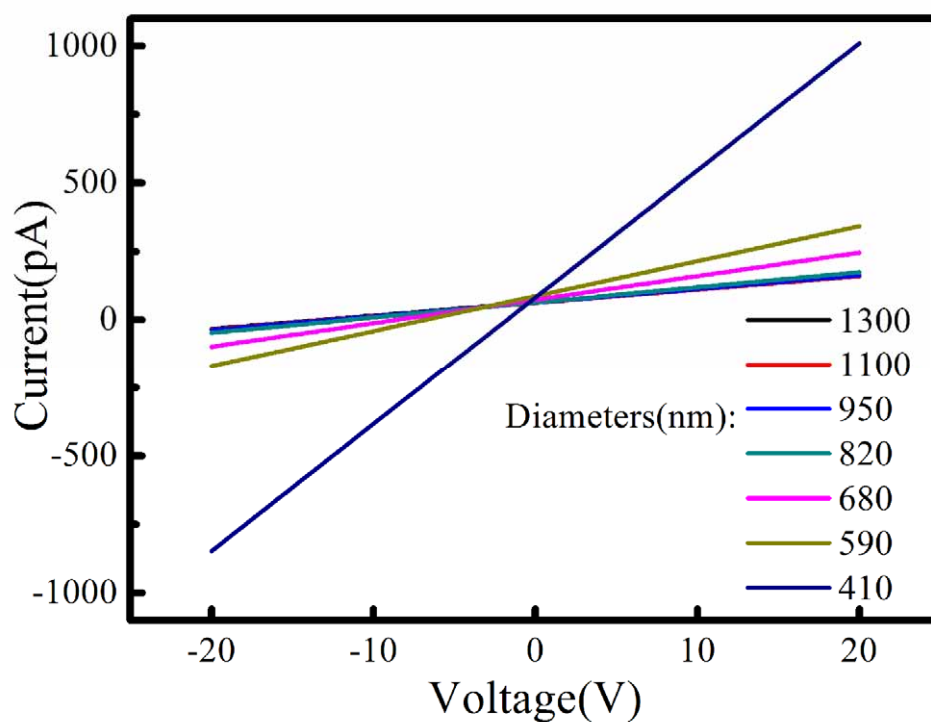


Figure S1 Current-voltage (I-V) characteristics from each data point in Figure 3,  
recorded on the Ta/ZnO/Ta structure.